

## N - CHANNEL ENHANCEMENT MODE SINGLE FEATURE SIZE™ POWER MOSFET

### TARGET DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP16NE06L	60 V	< 0.12 Ω	16 A
STP16NE06LFP	60 V	< 0.12 Ω	11 A

- TYPICAL R<sub>DS(on)</sub> = 0.09 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- 175°C OPERATING TEMPERATURE
- HIGH dV/dt CAPABILITY
- APPLICATION ORIENTED CHARACTERIZATION

### DESCRIPTION

This Power Mosfet is the latest development of SGS-THOMSON unique "Single Feature Size" process whereby a single body is implanted on a strip layout structure. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

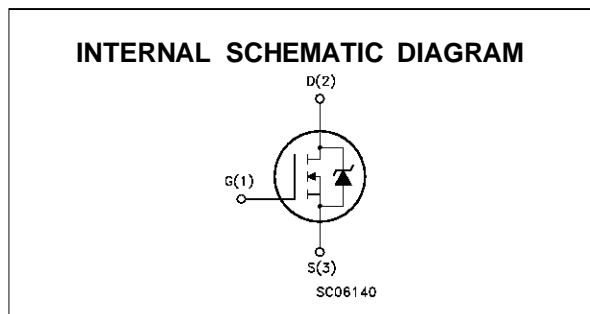
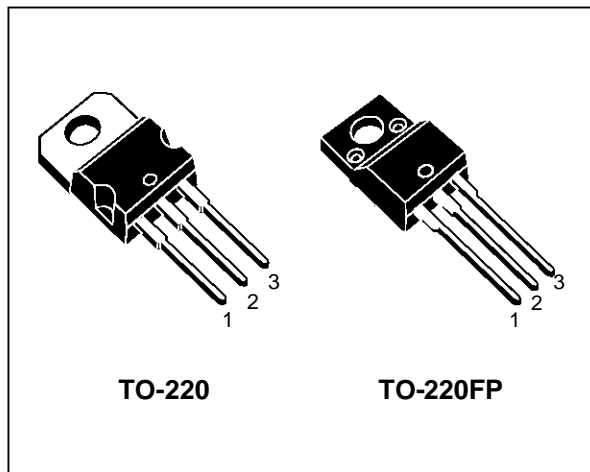
### APPLICATIONS

- DC MOTOR CONTROL
- DC-DC & DC-AC CONVERTERS
- SYNCHRONOUS RECTIFICATION

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP16NE06L	STP16NE06LFP	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60		V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	60		V
V <sub>GS</sub>	Gate-source Voltage	± 15		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	16	11	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	10	7	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	64	64	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	60	30	W
	Derating Factor	0.4	0.2	W/°C
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	—	2000	V
dV/dt	Peak Diode Recovery voltage slope	6		V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 175		°C
T <sub>j</sub>	Max. Operating Junction Temperature	175		°C

(•) Pulse width limited by safe operating area



(1) I<sub>SD</sub> ≤ 16 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

## STP16NE06L/FP

### THERMAL DATA

		TO-220	TO-220FP		
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	2.5	5	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5		°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ	0.5		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300		°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	16	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)	80	mJ

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>c</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 15V			æ 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 5V I <sub>D</sub> = 8 A V <sub>GS</sub> = 10V I <sub>D</sub> = 8 A		0.090	0.12	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	16			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 8 A		6		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		800		pF
C <sub>oss</sub>	Output Capacitance			100		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			50		pF

**ELECTRICAL CHARACTERISTICS** (continued)

## SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 30\text{ V}$ $I_D = 8\text{ A}$				ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$				ns
$Q_g$	Total Gate Charge	$V_{DD} = 40\text{ V}$ $I_D = 16\text{ A}$ $V_{GS} = 5\text{ V}$				nC
$Q_{gs}$	Gate-Source Charge					nC
$Q_{gd}$	Gate-Drain Charge					nC

## SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 48\text{ V}$ $I_D = 16\text{ A}$				ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$				ns
$t_c$	Cross-over Time					ns

## SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current					A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)					A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 16\text{ A}$ $V_{GS} = 0$			1.5	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 16\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$				ns
$Q_{rr}$	Reverse Recovery Charge					$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current					A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

Fig. 1: Unclamped Inductive Load Test Circuit

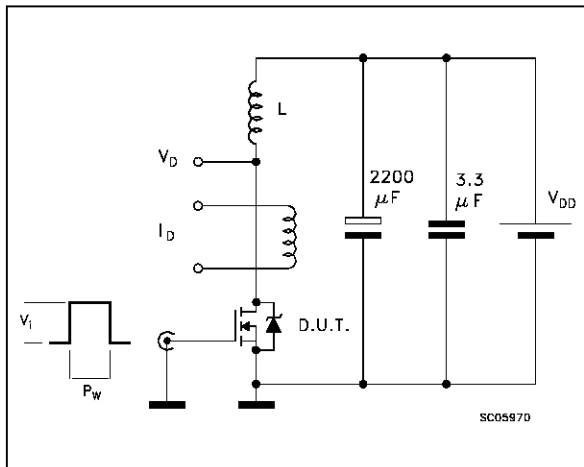


Fig. 2: Unclamped Inductive Waveform

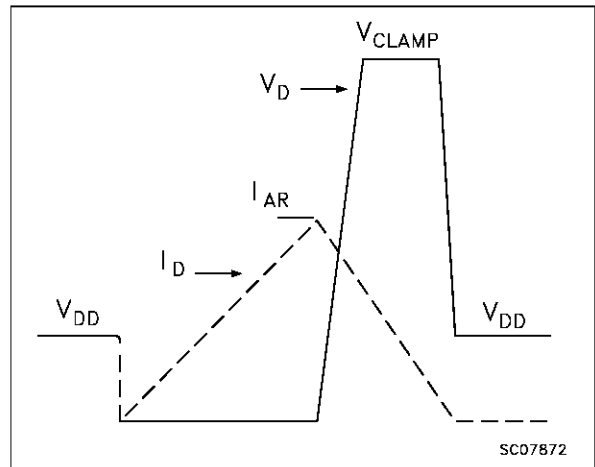


Fig. 3: Switching Times Test Circuits For Resistive Load

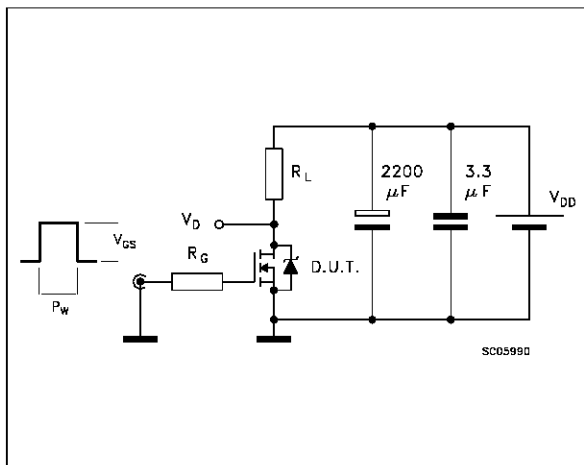


Fig. 4: Gate Charge test Circuit

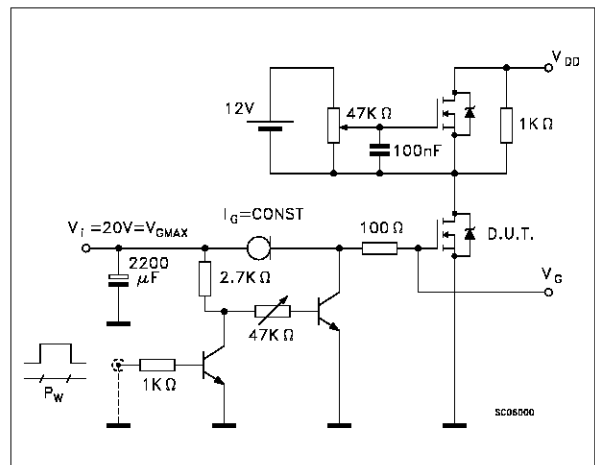
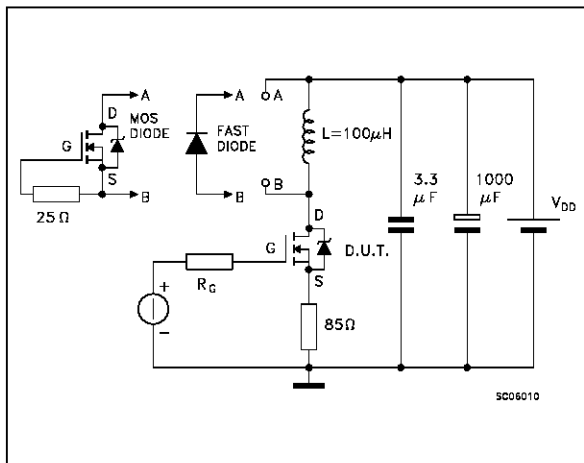
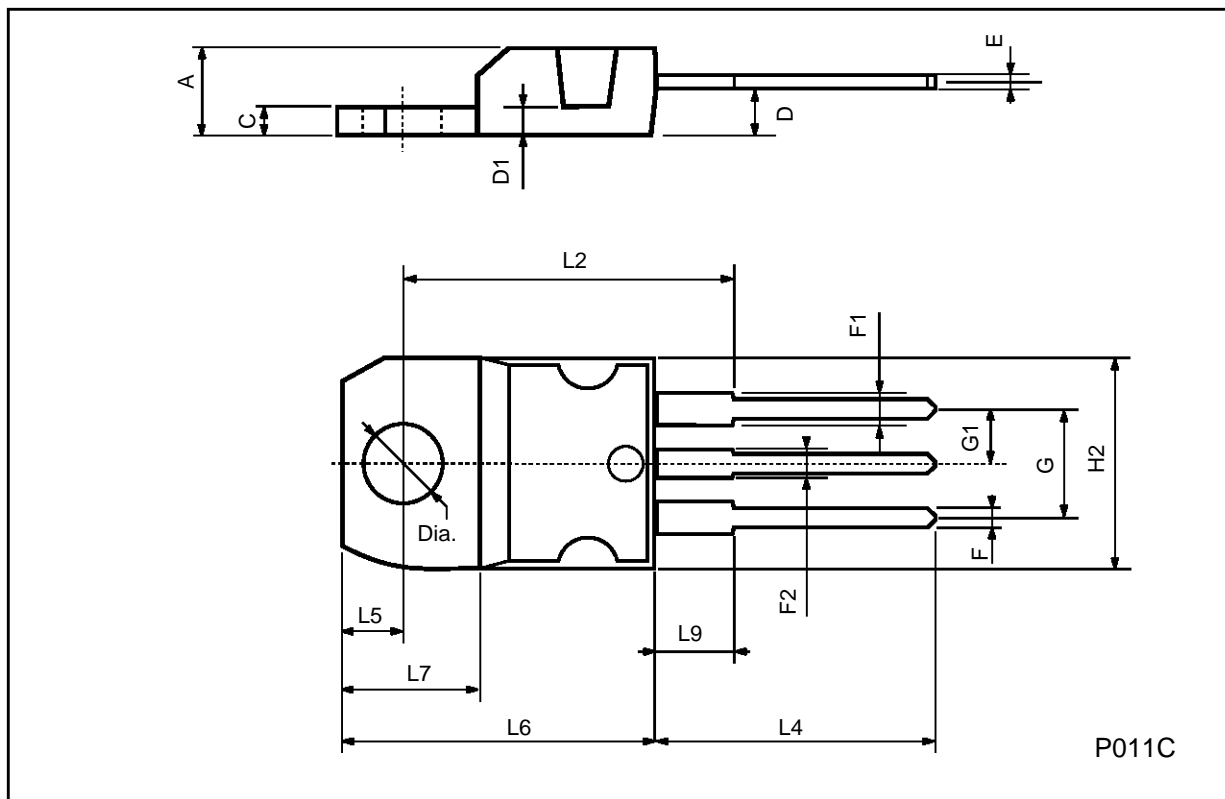


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



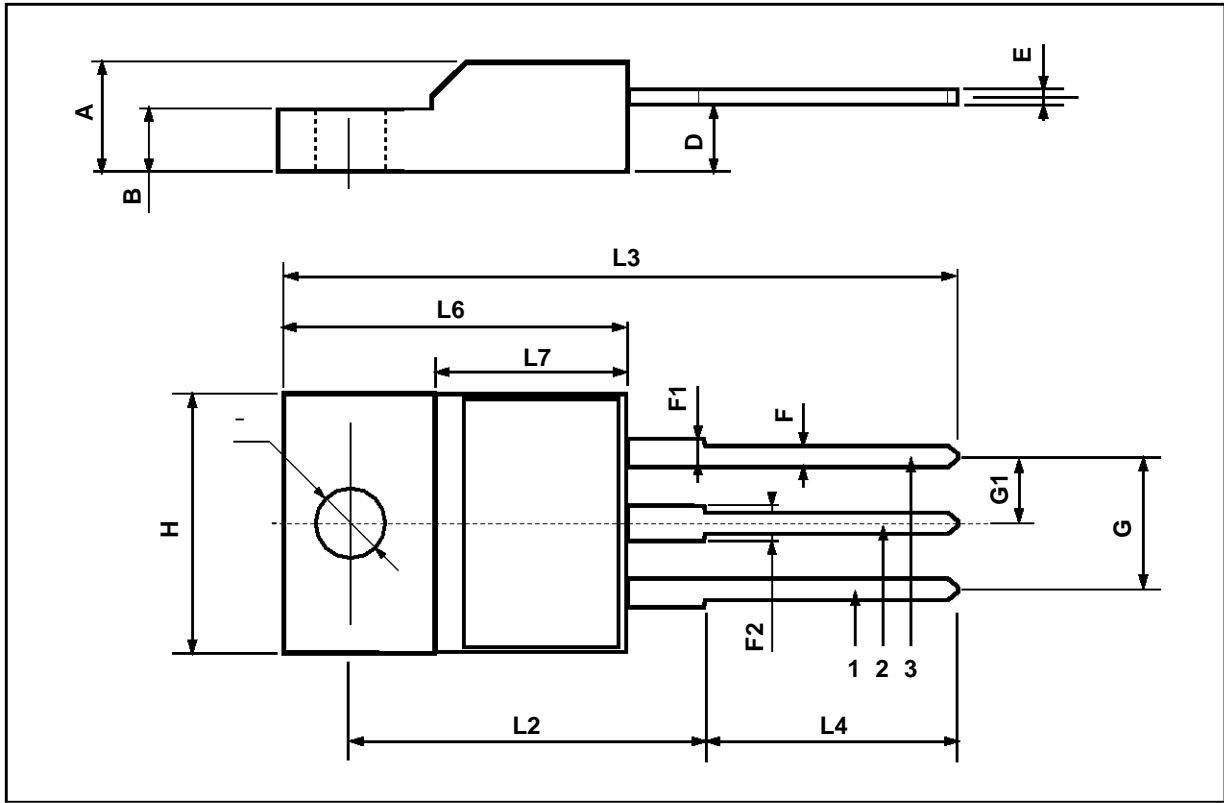
## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



**TO-220FP MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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